## MCH6436

## Power MOSFET 30V, 34mΩ, 6A, Single N-Channel



#### Features

- Low On-Resistance
- 1.8V Drive
- High Speed Switching
- ESD Diode-Protected Gate

**Thermal Resistance Ratings** 

When mounted on ceramic substrate

Junction to Ambient

 $(1500 \text{mm}^2 \times 0.8 \text{mm})$ 

Parameter

• Pb-Free and RoHS Compliance

#### **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

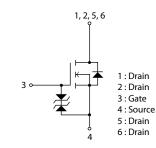
Parameter	Symbol	Value	Unit				
Drain to Source Voltage	V <sub>DSS</sub>	30	V				
Gate to Source Voltage	V <sub>GSS</sub>	±12	V				
Drain Current (DC)	ID	6	А				
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	I <sub>DP</sub>	24	A				
Power Dissipation When mounted on ceramic substrate (1500mm <sup>2</sup> × 0.8mm)	PD	1.5	W				
Junction Temperature	Tj	150	°C				
Storage Temperature	Tstg	–55 to +150	°C				

Symbol

 $R_{\theta JA}$ 

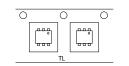
# VDSS RDS(on) Max ID Max 34mΩ@ 4.5V 49mΩ@ 2.5V 6A 69mΩ@ 1.8V 69mΩ@ 1.8V 6A

#### Electrical Connection N-Channel



#### Packing Type : TL

#### Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

83.3

Unit

°C/W

Value

#### **ORDERING INFORMATION**

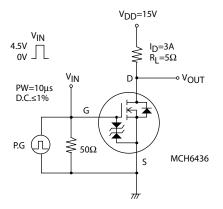
See detailed ordering and shipping information on page 5 of this data sheet.

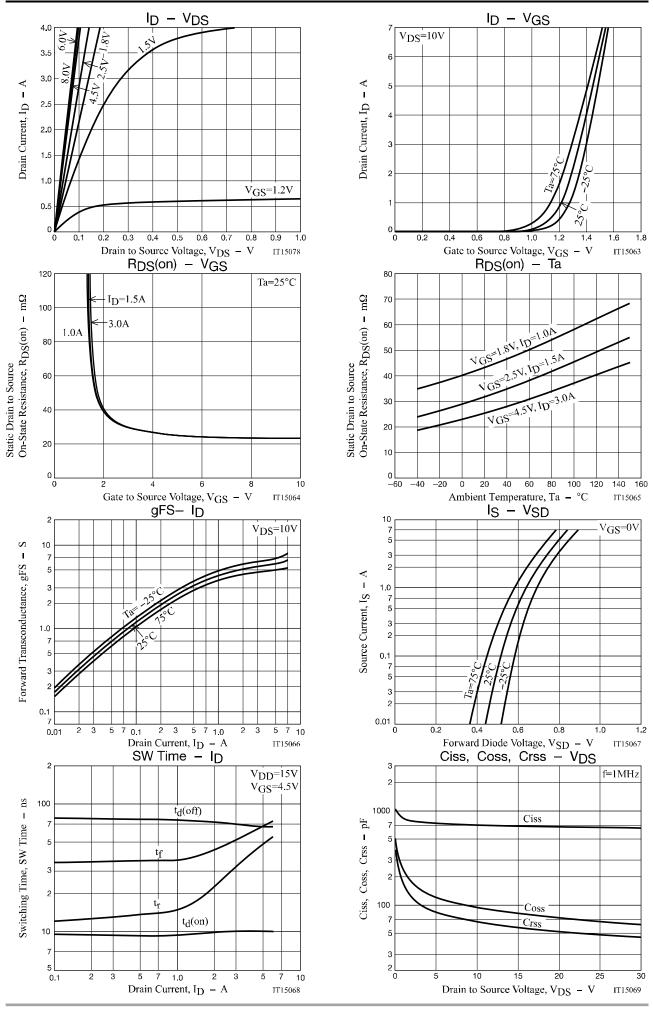
#### **Electrical Characteristics** at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions		Value		
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	$V_{GS}=\pm 8V, V_{DS}=0V$			±10	μΑ
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =3A		5.5		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =3A, V <sub>GS</sub> =4.5V		26	34	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =1.5A, V <sub>GS</sub> =2.5V		35	49	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =1A, V <sub>GS</sub> =1.8V		46	69	mΩ
Input Capacitance	Ciss	 V <sub>DS</sub> =10V, f=1MHz		710		pF
Output Capacitance	Coss			95		pF
Reverse Transfer Capacitance	Crss			65		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit		11		ns
Rise Time	tr			33		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)			70		ns
Fall Time	tf			52		ns
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A		7.5		nC
Gate to Source Charge	Qgs			1.3		nC
Gate to Drain "Miller" Charge	Qgd	1		1.5		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =6A, V <sub>GS</sub> =0V		0.82	1.2	V

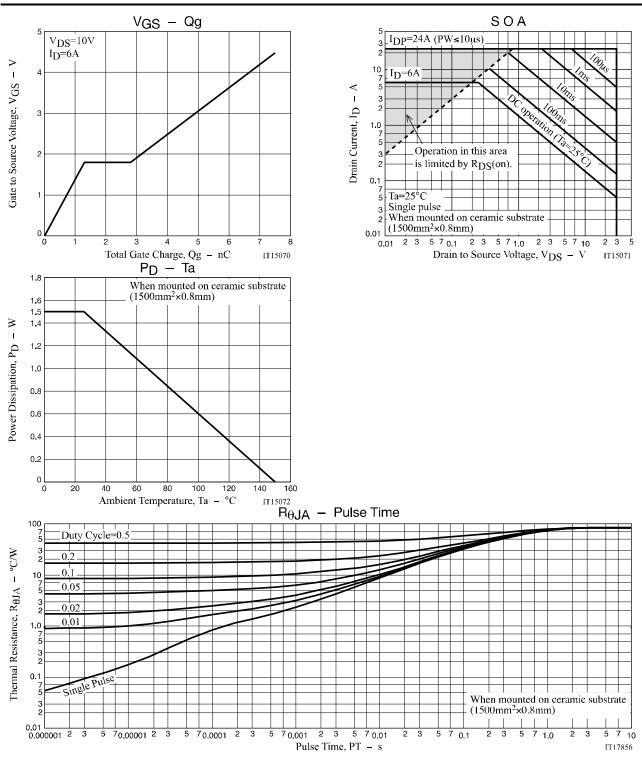
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **Switching Time Test Circuit**





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#### Package Dimensions

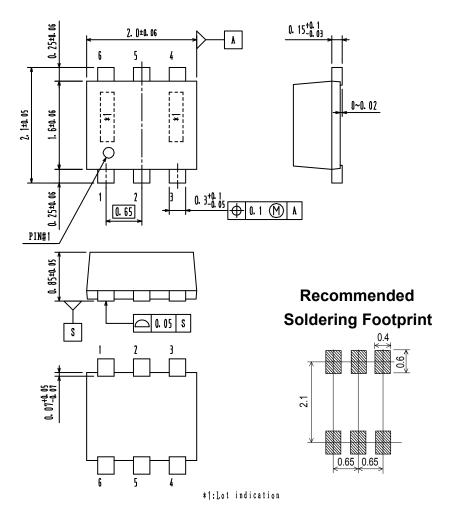
MCH6436-TL-E / MCH6436-TL-W

#### MCPH6

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unit : mm

- 1 : Drain
- 2 : Drain
- 3 : Gate
- 4 : Source
- 5 : Drain
- 6 : Drain



#### **ORDERING INFORMATION**

Device	Package	Shipping	Note
MCH6436-TL-E	MCPH6 SC-88FL,SC-70-6,SOT-363		Pb-Free
MCH6436-TL-W		3,000 pcs. / Tape & Reel	Pb-Free and Halogen Free

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

### Note on usage : Since the MCH6436 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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